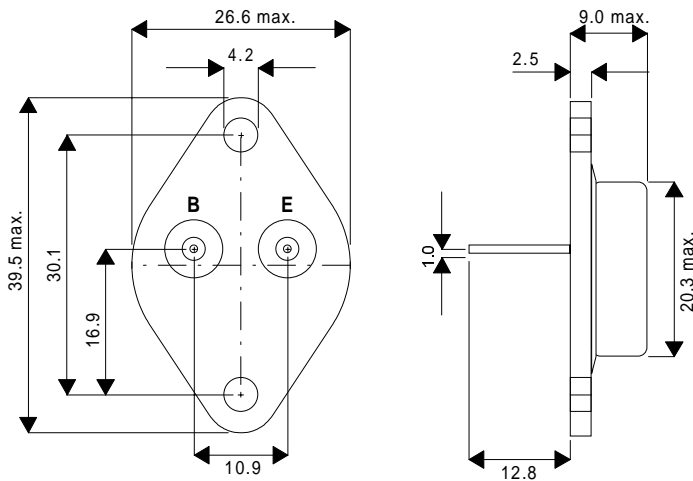


**MECHANICAL DATA**  
 Dimensions in mm

**NPN EPITAXIAL BASE  
 DARLINGTON POWER  
 TRANSISTOR**



**NPN epitaxial base transistors in monolithic Darlington circuit for audio output stages and general amplifier and switching applications.**

**PNP complements are:  
 BDX66, BDX66A, BDX66B, BDX66C.**

**TO3 Package.**  
 Case connected to collector.

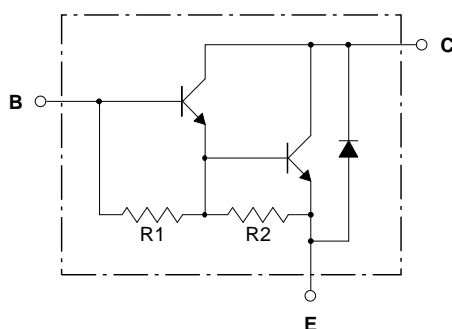
**ABSOLUTE MAXIMUM RATINGS** ( $T_{case}=25^{\circ}C$  unless otherwise stated)

		<b>BDX 67</b>	<b>BDX 67A</b>	<b>BDX 67B</b>	<b>BDX 67C</b>	
$V_{CEO}$	Collector - emitter voltage (open base)	60	80	100	120	V
$V_{CBO}$	Collector - base voltage (open emitter)	80	100	120	140	V
$V_{EBO}$	Emitter - base voltage (open collector)	5	5	5	5	V
$I_C$	Collector current	16				A
$I_{CM}$	Collector current (peak)	20				A
$I_B$	Base current	250				mA
$P_{tot}$	Total power dissipation at $T_{mb}=25^{\circ}C$	150				W
$T_j$	Maximum junction temperature	200				$^{\circ}C$
$T_{stj}$	Storage junction temperature	-65 to +200				$^{\circ}C$
$R_{th\ j-mb}$	Thermal resistance, junction to mounting base.	1.17				K/W

**ELECTRICAL CHARACTERISTICS** ( $T_j = 25^\circ\text{C}$ , unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit.
$I_{CBO}$ Collector cut-off current	$I_E = 0, V_{CB} = V_{CEOmax}$ $I_E = 0, V_{CB} = \frac{1}{2}V_{CB0max}, T_j = 200^\circ\text{C}$			1 5	mA
$I_{CEO}$ Collector cut-off current	$I_B = 0, V_{CE} = \frac{1}{2}V_{CEOmax}$			1	mA
$I_{EBO}$ Emitter cut-off current	$I_C = 0, V_{EB} = 5\text{V}$			5	mA
$h_{FE}$ D.C. current gain (note 1)	$I_C = 1\text{A}, V_{CE} = 3\text{V}$		5200		
	$I_C = 10\text{A}, V_{CE} = 3\text{V}$	1000			
	$I_C = 16\text{A}, V_{CE} = 3\text{V}$		4000		
$V_{BE}$ Base - emitter voltage (note 1)	$I_C = 10\text{A}, V_{CE} = 3\text{V}$			2.5	V
$V_{CEsat}$ Collector - emitter saturation voltage	$I_C = 10\text{A}, I_B = 40\text{mA}$			2	V
$C_c$ Collector capacitance	$I_E = I_e = 0, V_{CB} = 10\text{V} f = 1\text{MHz}$		300		pF
$f_{hfe}$ Cut-off frequency	$I_C = 5\text{A}, V_{CE} = 3\text{V}$		50		kHz
$E_{(BR)}$ Turn-off breakdown energy with inductive load	$-I_{Boff} = 0, I_{CC} = 7.8\text{ A}$ $t_p = 1\text{ms}, \delta < 1\%$	150			mJ
$h_{fe}$ Small signal current gain	$I_C = 5\text{A}, V_{CE} = 3\text{V}, f = 1\text{MHz}$		20		V
$V_F$ Diode, forward voltage	$I_F = 10\text{A}$		2.5		

Note 1: Measured under pulse conditions ,  $t_p < 300\mu\text{s}, \delta < 2\%$



R1 typ.  $3\text{K}\Omega$   
R2 typ.  $80\Omega$

Circuit Diagram